

<b>FORM PTO-1449 U.S. Department of Commerce</b> <b>Patent and Trademark Office</b>  <b>LIST OF DOCUMENTS CITED BY APPLICANT</b>  (Use several sheets if necessary)				<b>Attorney Docket Number</b> 5308-278		<b>Serial No.</b> To be assigned	
				<b>Applicants:</b> Ryu et al.			
				<b>Filing Date:</b> Concurrently herewith		<b>Group:</b> Unknown	
U. S. PATENT DOCUMENTS							
Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
TTW	1	3,047,439	07/31/62	H.J. Van Daal et al.			
	2	3,121,829	02/18/64	A. Huizing et al.			
	3	3,628,187	12/04/71	DeLoach, Jr. et al.	331	107	
	4	4,096,622	06/27/78	MacIver	29	578	
	5	4,329,699	05/11/82	Ishihara et al.	357	2	
	6	4,607,270	08/19/86	Iesaka	357	15	
	7	4,638,551	01/27/87	Einthoven	29	571	1
	8	4,720,734	01/19/88	Amemiya et al.	357	15	
	9	4,738,937	04/19/88	Parsons	437	180	
	10	4,742,377	05/03/88	Einthoven	357	15	
	11	4,762,806	08/09/88	Suzuki et al.	437	100	
	12	4,765,845	08/23/88	Takada et al.	136	258	
	13	4,816,879	03/28/89	Ellwanger	357	15	
	14	4,866,005	09/12/89	Davis et al.	437	100	
	15	4,875,083	10/17/89	Palmour	357	23.6	
	16	4,901,120	2/13/90	Weaver et al.	357	15	
	17	4,907,040	03/06/90	Kobayashi et al.	357	4	
	18	4,918,497	04/17/90	Edmond	357	17	
	19	5,471,072	11/28/95	Papanicolaou	257	77	
	20	5,712,502	1/27/98	Mitlehner	257	341	
	21	5,789,311	8/4/98	Ueno et al.	438	573	
	22	5,801,836	08/01/98	Bakowski et al.	257	487	
	23	5,907,179	05/25/99	Losehand et al.	257	475	
	24	5,914,500	06/22/99	Bakowski et al.	257	77	
TTW	25	5,932,894	08/03/99	Bakowski et al.	257	76	

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TTN	26	5,977,605	11/02/99	Bakowsky et al.	257	496	
	27	6,002,159	12/14/99	Bakowski et al.	257	493	
	28	6,005,261	12/21/99	Konstantinov	257	77	
	29	6,040,237	03/21/00	Bakowski et al.	438	521	
	30	6,083,814	07/4/00	Nilsson et al.	438	519	
	31	6,110,813	08/29/00	Ota et al.	438	597	
	32	6,191,015 B1	02/20/01	Losehand et al.	438	570	
	33	6,313,482 B1	11/6/01	Baliga	257	77	
	34	6,320,205 B1	11/20/01	Pfirsch et al.	257	77	
TTN	35	6,573,128 B1	06/03/03	Singh	438	167	

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		Document Number	Date	Country	Class	Subclass	Translation Yes   No
TTN	36	WO97/087 54	03/06/97	PCT			
	37	63-133569	06/06/88	Japan			
	38	62-279672	06/06/88	Japan			
	39	58-148469	03/09/83	Japan			
	40	EP111168 8A1	06/27/01	EPO			
TTN	41	WO 96/03774	02/08/96	PCT			

TTN	42	Katsunori Ueno, Tatsue Urushidani, Kouichi Hahimoto, and Yasukazu Seki. "The Guard -Ring Termination for the High-Voltage SiC Schottky Barrier Diodes." <i>IEEE Electron Device Letters</i> . Vol. 16. No. 7, July 1995.					
TTN	43	Singh, R. and J.W. Palmour, "Planar Terminations in 4H-SiC Schottky Diodes with Low Leakage and High Yields," <i>IEEE International Symposium on Power Semiconductor Devices and ICs</i> , 1997.					

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		Filing Date: Concurrently herewith	Group: Unknown
TDW	44	Kosiachenko, L.A. and E.F. Kukhta, V.M. Skiliarchuk, "Light Emission from Metal at Forward Bias of a Schottky Diode," <i>Zhurnal tekhnicheskoi fiziki [Journal of Technical Physics]</i> , Vol. 54, No. 6, 1984.	
	45	Kyoritsu Shuppan Kabushiki Kaisha, <i>Crystallography Handbook</i>	
	46	<i>The Electrical Engineering Handbook</i> , Richard C. Dorf, editor, Second Edition, CRC/IEEE Press.	
	47	Sze, S.M. <i>Physics of Semiconductor Devices</i> , John Wiley & Sons, p. 250-254.	
	48	Streetman, B.G. <i>Solid State Electronic Devices</i> . Second Edition, Prentice-Hall, 1980, pp. 192-3, 201, 443	
	49	Saidov, M.S., Kh. A. Shamuratov, and A. Umurzakov. "Current-voltage characteristics of silicon carbide heterojunctions." <i>Soviet Physics of Semiconductors</i> . Vol. 13, No. 9, September, 1979, pp. 1054-1056.	
	50	Pelletier, J., D. Gervais, and C. Pomot. "Application of Wide Gap Semiconductors to Surface Ionization: Work Functions of AlN and SiC Crystals." <i>Journal of Applied Physics</i> . Vol. 55, No. 4. February 15, 1984, pp. 994-1002.	
	51	Edmond, J.A., J. Ryu, J.T. Glass, and R.F. Davis. "Electrical Contacts to Beta Silicon Carbide Thin Films." <i>Journal of the Electromechanical Society</i> . Vol. 135, No. 2, February 1988, pp. 359-362.	
	52	Waldrop, J.R. and R.W. Grant. "Formation and Schottky barrier height of metal contacts to $\beta$ -SiC." <i>Applied Physics Letters</i> . Vol. 56, No. 6, February 5, 1990, pp. 557-559.	
	53	Ioannou, D.E. and N.A. Papanicolaou. "Deep Level Transient Spectroscopy of $\beta$ -SiC Layers." <i>Abstracts</i> . Fourth National Review Meeting On Growth and Characterization of SiC and Its Employment in Semiconductor Applications.	
	54	Anikin, M.M. et al. "Electrostatic properties of SiC-6H structures with an abrupt pin junction." <i>Soviet Physics Semiconductors</i> . Jan. 1988, Vol. 22(1): pp. 80-83.	
	55	Glover, G.H. "Charge Multiplication in Au-SiC (6H) Schottky Junctions." <i>Journal of Applied Physics</i> . November, 1975, Vol. 46, No. 11: pp. 4842-4844	
	56	Ioannou et al. "The Effect of Heat Treatment on Au Schottky Contacts on $\beta$ -SiC." <i>IEEE Transactions on Electron Devices</i> . August, 1979, Vol. Ed-34, No. 8: pp. 1694-1699.	
	57	Violin, E.E., et al. "Light Emitting Devices Based on Silicon Carbide." <i>Silicon Carbide</i> . 1973, p. 565. (edited by Marshall, Faust, Ryan).	
	58	Powell, J.A. "Silicon Carbide: Progress in Crystal Growth." <i>Material Research Society Symposium Proceedings</i> . 1987, Vol. 97: pp.159-168.	
	59	Konstantinov, A.O. "Ionization Rates and Critical Fields in 4H Silicon Carbide," <i>Appl. Phys. Lett.</i> Vol. 71, No. 1, July 1997, pp. 90-92.	
	60	Appels et al. "High-voltage thin layer devices (RESURF devices)," <i>IEDM Tech. Dig.</i> , 1979, pp. 238-41.	
	61	Li et al. "Theoretical and Experimental Study of 4H-SiC Junction Edge Termination," <i>Materials Science Forum</i> , Vols. 338-342 (2000), pp. 1375-8.	
	62	Merchant et al. "Realization of High Breakdown Voltage (>700V) in Thin SOI Devices," <i>Tech. Digest of ISPSD '91</i> , pp. 31-4.	
TDW	63	Yilmaz, Hamza, "Optimization and Surface Charge Sensitivity of High Voltage Blocking Structures with Shallow Junctions," <i>IEEE Transactions on Electron Devices</i> , Vol. 38, No. 3, July 1991, pp. 1666-75.	

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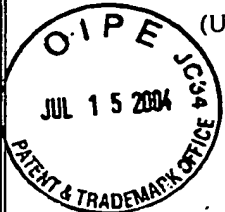
<b>FORM PTO-1449 U.S. Department of Commerce Patent and Trademark Office</b>				<b>Attorney Docket Number</b> 5308-278		<b>Serial No.</b> 10/731,860	
<b>LIST OF DOCUMENTS CITED BY APPLICANT</b> (Use several sheets if necessary)				<b>Applicants:</b> Ryu et al.			
				<b>Filing Date:</b> December 9, 2003		<b>Group:</b> 2811	
<b>U. S. PATENT DOCUMENTS</b>							
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<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Subclass	Translation Yes   No
<b>OTHER DOCUMENTS</b>							
<div style="font-size: 1.5em; font-family: cursive;">TTN</div>	1	Kinoshita et al. "Guard Ring Assisted RESURF: A New Termination Structure Providing Stable and High Breakdown Voltage for SiC Power Devices," <i>Tech. Digest of ISPSD '02</i> , pp. 253-6.					

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<div style="display: flex; align-items: center;"> <div style="text-align: center; margin-right: 20px;">  </div> <div>             (Use several sheets if necessary)           </div> </div>							
Applicants: Ryu et al.							
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<b>U. S. PATENT DOCUMENTS</b>							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
TTN	1.	5,994,189	11/30/99	Akiyama	438	268	